L Number	Hits	Search Text	DB	Time stamp
-	1192	@ad<=20010104 and 'heating substrate' and 'amorphous silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 13:46
-	943	((438/486) or (438/482)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:05
-	71	(((438/486) or (438/482)).CCLS.) and @ad<=20010104 and 'heating substrate' and 'amorphous silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:00
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'heating substrate' and 'amorphous silicon' and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:18
-	2	(((438/486) or (438/482)).CCLS.) and MILC and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:36
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and MILC and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:06
-	0	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'while depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:01
-	181	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	109	(@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating') and 'depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	14	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'amorphous silicon' and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:10
-	303	(((438/486) or (438/482)).CCLS.) and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:37
-	52	(((438/486) or (438/482)).CCLS.) and 'low temperature' and 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:37
-	0	@ad<=20010104 and heating adj1 substrate with depositing same metal and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:51

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–	58	@ad<=20010104 and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:18
–	0	@ad<=20010104 and heating adj1 substrate adj1 while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:54
–	0	@ad<=20010104 and heat adj1 substrate adj1 while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:54
–	3	@ad<=20010104 and heat adj1 substrate same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:56
–	74	@ad<=20010104 and heating adj1 substrate same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 14:15
–	15	@ad<=20010104 and 'hot metallization'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 14:16
–	191	@ad<=20010104 and 'amorphous silicon' same 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:55
–	12	@ad<=20010104 and 'amorphous silicon' same 'heating substrate' same 'metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:40
–	3778	((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:42
–	54	(((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.) and @ad<=20010104 and 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:56
–	2	"20020137310"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:55
–	447	@ad<=20010104 and low adj temperature adj crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:35
–	318928	(("257") or ("438")).CLAS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 13:59
–	124	(@ad<=20010104 and low adj temperature adj crystallization) and 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:13

-	1	("6524662").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:07
-	28	(@ad<=20010104 and low adj temperature adj crystallization) and heat adj substrate and 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:14
-	9	@ad<=20010104 and deposit adj nickel same 'heat' same 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:39
-	6	@ad<=20010104 and 'heated' with 'substrate' same deposit adj nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:40
-	62	@ad<=20010104 and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:26
-	3	("6524662").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:22
-	24	@ad<=20010104 and Joo-seung.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:27
-	39	Joo-seung-ki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:27
-	2	("6097037").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:57
-	231	@ad<=20010104 and 'amorphous silicon' same 'nickel' same 'sputtering'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:02
-	53	@ad<=20010104 and 'amorphous silicon' with 'nickel' with 'sputtering'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:19
-	8	@ad<=20010104 and 'amorphous silicon' with 'nickel' with 'sputtering' with 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:22
-	222	@ad<=20010104 and 'sputtering' with 'temperature' same 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:22
-	100	@ad<=20010104 and 'sputtering' with 'temperature' with 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:27

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		5	@ad<=20010104 and 'nickel' with 'sputtering temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:49
-		0	@ad<=20010104 and 'nickel' with 'oxidation' adj1 'stable' with 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:48
-		6	@ad<=20010104 and 'nickel' with 'oxidation' adj1 'stable'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:48
-		11	@ad<=20010104 and 'nickel' same 'sputtering temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:55
-		93	@ad<=20010104 and 'nickel' same 'oxidation temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:56
-		31	@ad<=20010104 and 'nickel' with 'oxidation temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:02
-		72	@ad<=20010104 and 'nickel' with 'silicidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:02
-		27	@ad<=20010104 and 'nickel' adj1 'silicidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:04
-		26	@ad<=20010104 and 'nickel' adj1 'silicidation' and 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:04
-		17	@ad<=20010104 and 'nickel' adj1 'silicidation' same 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:15
-		153	@ad<=20010104 and 'nickel' same 'silicon' with 'crystallized' same 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:16
-		64	@ad<=20010104 and 'nickel' same 'silicon' with 'crystallized' with 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:16
-		2	("5614291").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:22

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